

FDC638P

P-Channel 2.5V PowerTrench[®] Specified MOSFET

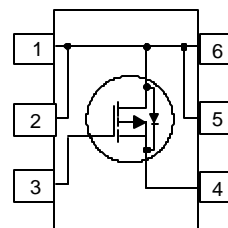
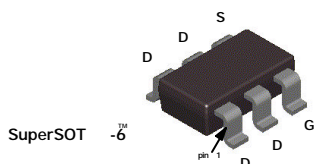
General Description

This PChannel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance

These devices are well suited for battery power applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

- -4.5 A, -20 V. $R_{DS(ON)} = 48\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
 $R_{DS(ON)} = 65\text{ m}\Omega$ @ $V_{GS} = -2.5\text{ V}$
- Low gate charge (10 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT™ -6 package: small footprint (72% smaller than standard SO-8; low profile (1mm thick)



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	-20	V
V _{GSS}	Gate-Source Voltage	±8	V
I _b	Drain Current – Continuous (Note 1a) – Pulsed	-4.5	A
		-20	
P _d	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.6	W
		0.8	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case (Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.638	FDC638P	7"	8mm	3000 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-14		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.8	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		3		mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -4.5\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -3.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -4.5\text{ A}, T_J = 125^\circ\text{C}$		39 52 54	48 65 72	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-20			A
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -4.5\text{ A}$		15		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1160		pF
C_{oss}	Output Capacitance			195		pF
C_{rss}	Reverse Transfer Capacitance			105		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		12	22	ns
t_r	Turn-On Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			33	53	ns
t_f	Turn-Off Fall Time			12	22	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -4.5\text{ A},$ $V_{GS} = -4.5\text{ V}$		10	14	nC
Q_{gs}	Gate-Source Charge			2.2		nC
Q_{gd}	Gate-Drain Charge			1.5		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				-1.3	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.3\text{ A}$ (Note 2)		-0.73	-1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



- a) 78°C/W when mounted on a 1 in^2 pad of 2 oz copper



- b) 156°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < $300\ \mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics

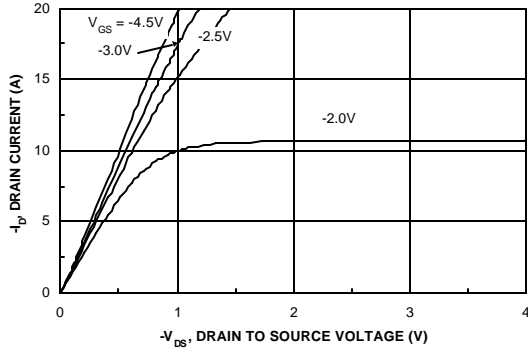


Figure 1. On-Region Characteristics.

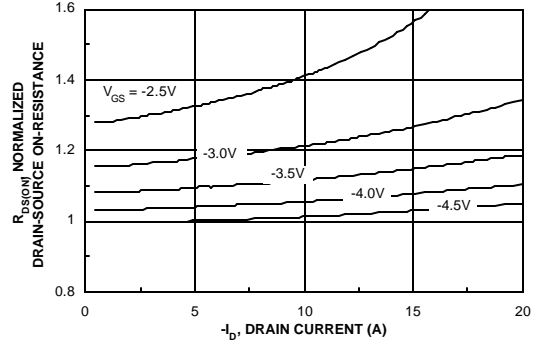


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

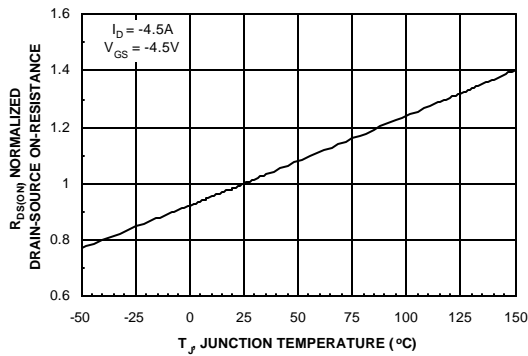


Figure 3. On-Resistance Variation with Temperature.

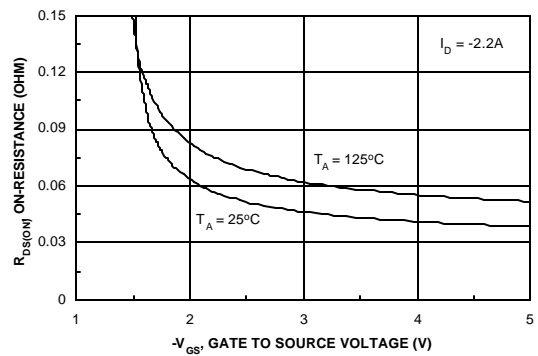


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

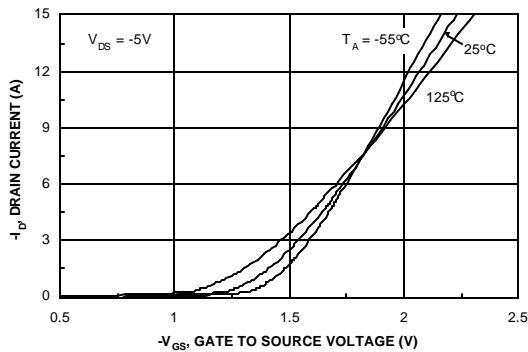


Figure 5. Transfer Characteristics.

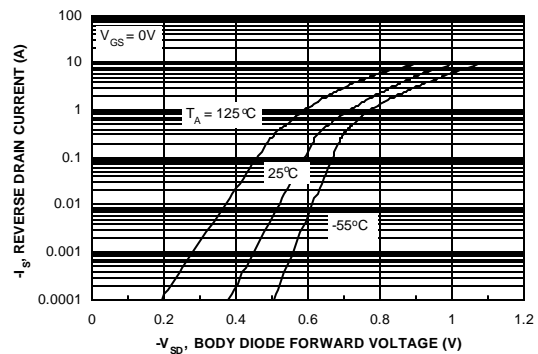


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

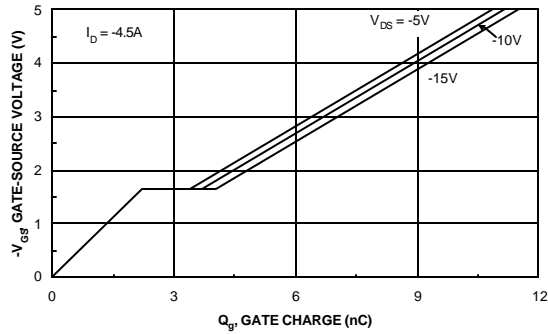


Figure 7. Gate Charge Characteristics.

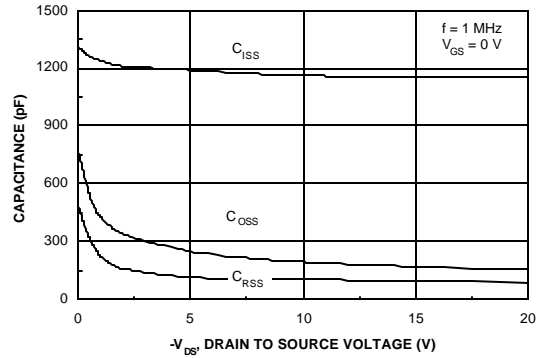


Figure 8. Capacitance Characteristics.

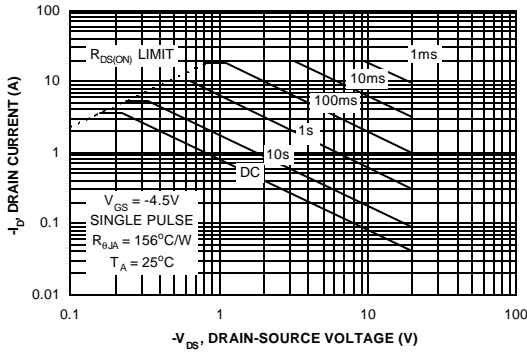


Figure 9. Maximum Safe Operating Area.

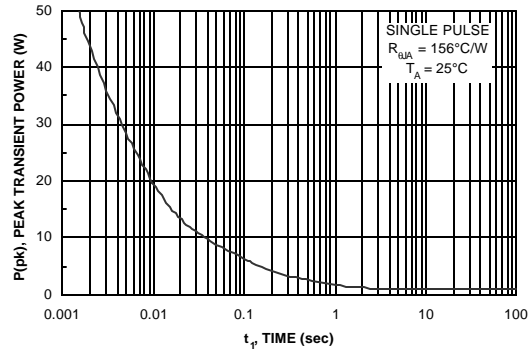


Figure 10. Single Pulse Maximum Power Dissipation.

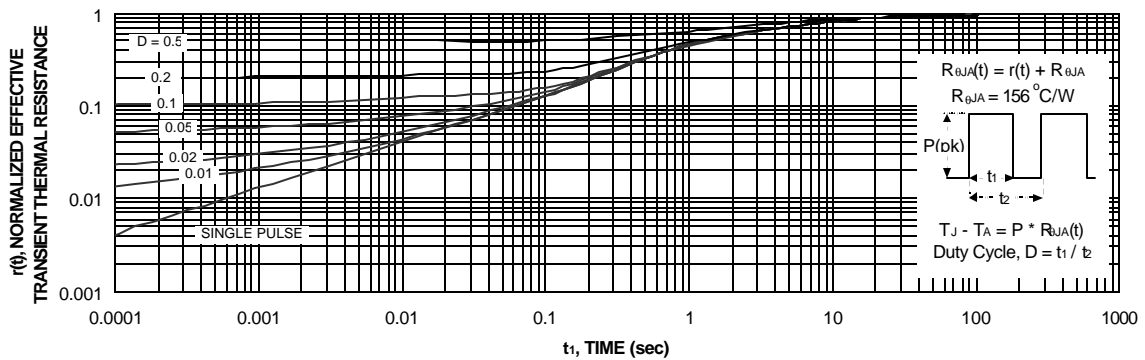


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b
Transient thermal response will change depending on the circuit board design.

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DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOMET TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
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